

Silicon NPN Power Transistors

2SC2611

DESCRIPTION

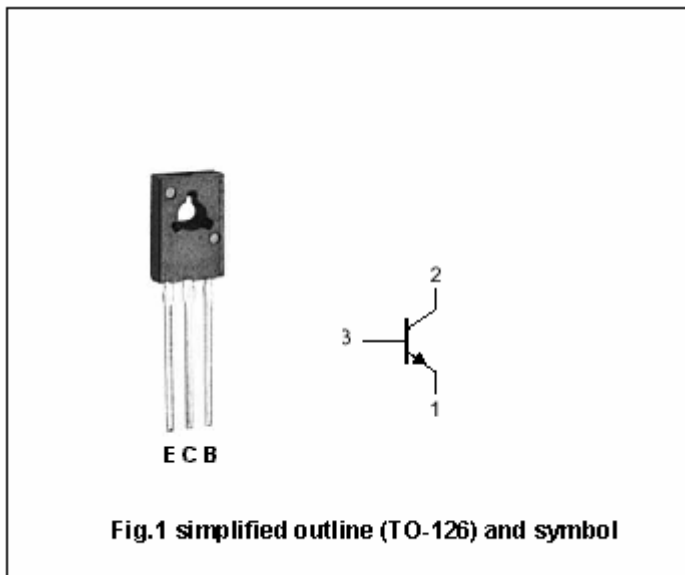
- With TO-126 package
- High breakdown voltage

APPLICATIONS

- For high voltage amplifier TV video output applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



ABSOLUTE MAXIMUM RATINGS(T_c=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	300	V
V _{CEO}	Collector-emitter voltage	Open base	300	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		0.1	A
P _C	Collector power dissipation	T _a =25℃	1.25	W
T _j	Junction temperature		150	℃
T _{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =1mA; R _{BE} =∞	300			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =10μA; I _E =0	300			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10μA; I _C =0	5			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =20mA; I _B =2mA			1.5	V
I _{CEO}	Collector cut-off current	V _{CE} =250V; R _{BE} =∞			1.0	μA
h _{FE}	DC current gain	I _C =20mA; V _{CE} =20V	30		200	
f _T	Transition frequency	I _C =20mA; V _{CE} =20V	50	80		MHz
C _{OB}	Collector output capacitance	I _E =0; V _{CB} =20V; f=1MHz			4.0	pF

